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Raghavendra Rao Juluri, Peter Gaiduk, John Lundsgaard Hansen, Arne Nylandsted Larsen, Brian Julsgaard

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Raghavendra Rao Juluri¹

Peter Gaiduk^{2, 3}

John Lundsgaard Hansen^{1, 2}

Arne Nylandsted Larsen^{1, 2}

Brian Julsgaard^{1, 2}

1Interdisciplinary Nanoscience Center (iNano), Aarhus University, Gustav Wieds Vej 14, DK-8000 Aarhus C, Denmark.

2Department of Physics and Astronomy, Aarhus University, Ny Munkegade 120, DK-8000 Aarhus C, Denmark.

3Department of Physical Electronics and Nanotechnologies, Belarussian State University, Praspyekt Nyezalyezhnastsi 4, 220030 Minsk, Belarus.

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